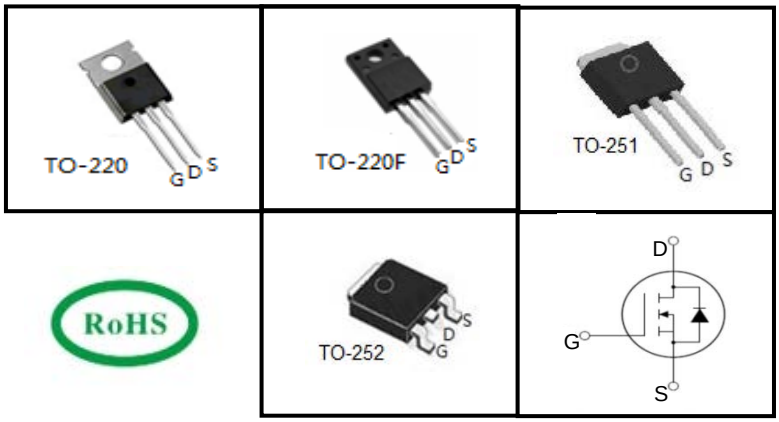
550V Super-Junction Power MOSFET

FEATURES

- Very low FOM $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- RoHS compliant



APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

Device Marking and Package Information				
Device	TPA55R2K9C	TPP55R2K9C	TPU55R2K9C	TPD55R2K9C
Package	TO-220F	TO-220	TO-251	TO-252
Marking	55R2K9C	55R2K9C	55R2K9C	55R2K9C

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted

Parameter		Symbol	Value		Unit
			TO-220,TO-251,TO-252	TO-220F	
Drain-Source Voltage (V_{GS} = 0V)		V_{DSS}	550		V
Continuous Drain Current		I_D	1.4		A
Pulsed Drain Current	(note1)	I_{DM}	4.2		A
Gate-Source Voltage		V_{GSS}	±30		V
Single Pulse Avalanche Energy	(note2)	E_{AS}	1.25		mJ
Avalanche Current	(note1)	I_{AR}	0.5		A
Repetitive Avalanche Energy	(note1)	E_{AR}	0.03		mJ
Power Dissipation (T_C = 25ºC)		P_D	12.3	6	W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55~+150		ºC

Thermal Resistance

Parameter	Symbol	Value		Unit
		TO-220,TO-251,TO-252	TO-220F	
Thermal Resistance, Junction-to-Case	R_{thJC}	10.2	20.8	K/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62	80	

Specifications T_J = 25ºC, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Value**			**Unit**
			Min.	**Typ.**	**Max.**	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	550	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 550V, V_{GS} = 0V, T_J = 25ºC	--	--	1	μA
		V_{DS} = 550V, V_{GS} = 0V, T_J = 150ºC	--	--	100	
Gate-Source Leakage	I_{GSS}	V_{GS} = ±30V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2.5	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	V_{GS} = 10V, I_D = 0.7A	--	2.5	2.9	Ω
Forward Transconductance (Note3)	g_{fs}	V_{DS} = 10V, I_D = 0.7A	--	1.0	--	S
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 50V, f = 1.0MHz	--	120	--	pF
Output Capacitance	C_{oss}		--	25	--	
Reverse Transfer Capacitance	C_{rss}		--	5	--	
Total Gate Charge	Q_g	V_{DD} = 400V, I_D = 1.4A, V_{GS} = 10V	--	4.1	--	nC
Gate-Source Charge	Q_{gs}		--	0.7	--	
Gate-Drain Charge	Q_{gd}		--	2.5	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 400V, I_D = 1.4A, R_G = 25Ω	--	49	--	ns
Turn-on Rise Time	t_r		--	17	--	
Turn-off Delay Time	$t_{d(off)}$		--	24	--	
Turn-off Fall Time	t_f		--	19	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	T_C = 25ºC	--	--	1.4	A
Pulsed Diode Forward Current	I_{SM}		--	--	5.6	
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = 1.4A, V_{GS} = 0V	--	0.9	1.2	V
Reverse Recovery Time	t_{rr}	V_R = 400V, I_F = I_S, di_F/dt = 100A/μs	--	76.6	--	ns
Reverse Recovery Charge	Q_{rr}		--	0.3	--	μC
Peak Reverse Recovery Current	I_{rrm}		--	3.1	--	A

Notes

1. Repetitive Rating: Pulse Width limited by maximum junction temperature
2. I_{AS} = 0.5A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 1%

Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics

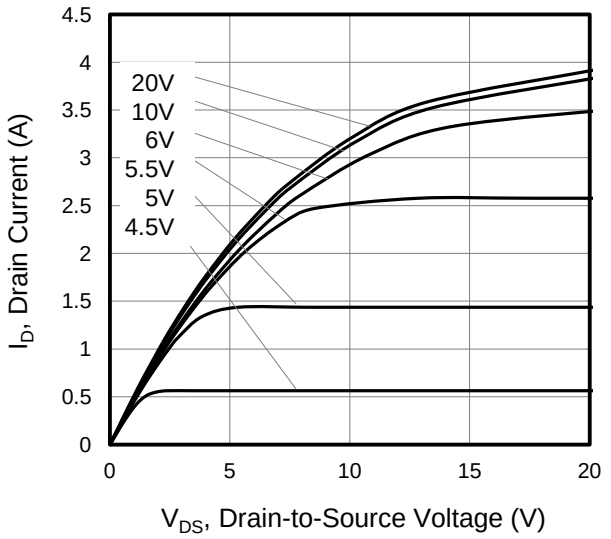


Figure 2. Transfer Characteristics

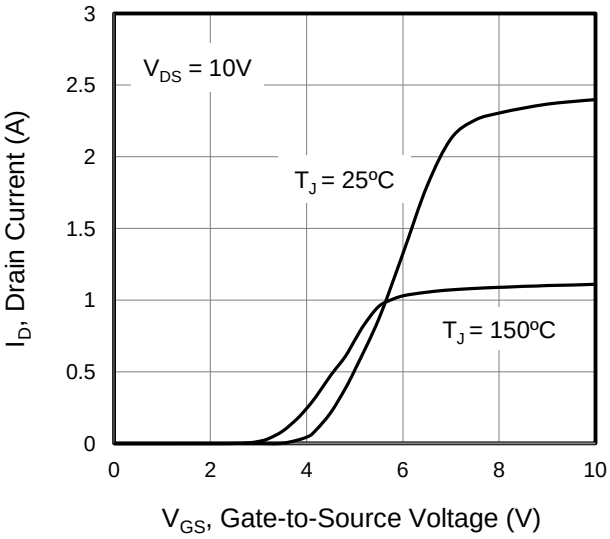


Figure 3. On-Resistance vs. Drain Current

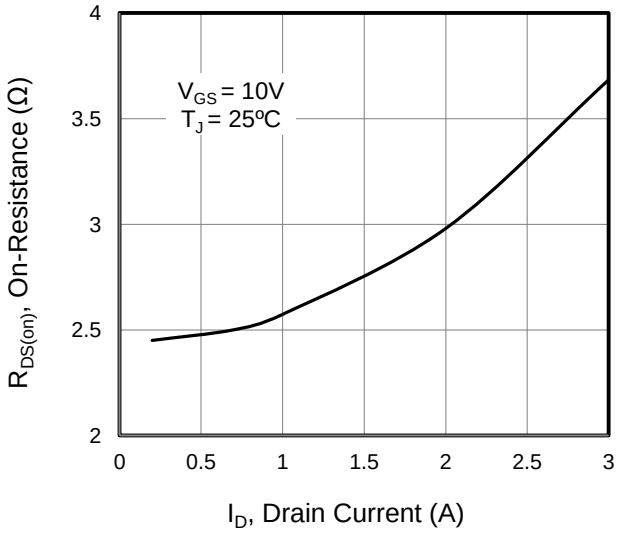


Figure 4. Capacitance

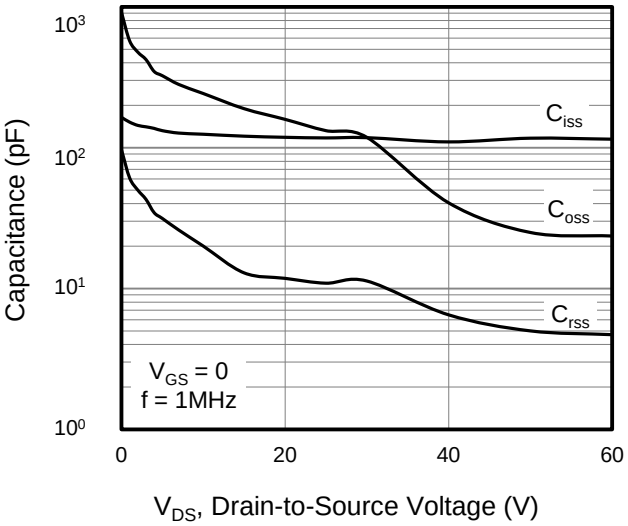


Figure 5. Gate Charge

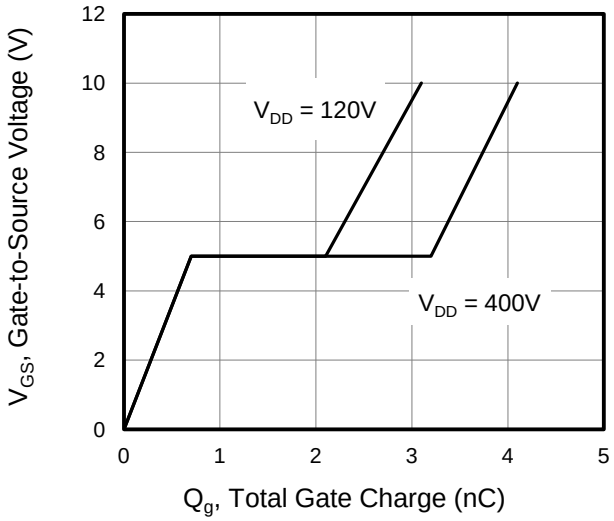
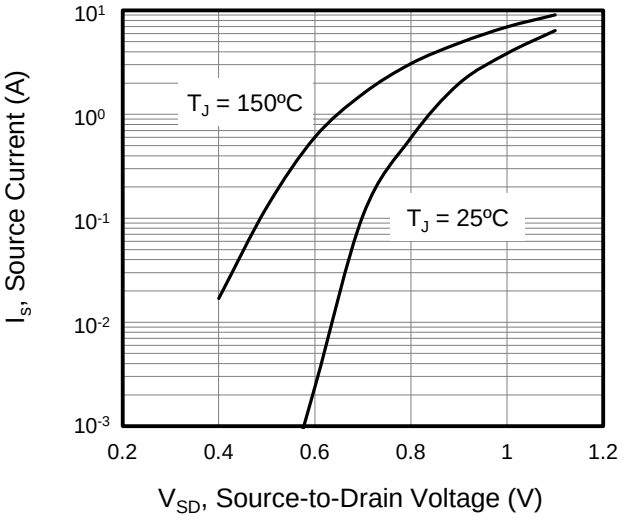


Figure 6. Body Diode Forward Voltage



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 7. On-Resistance vs. Junction Temperature

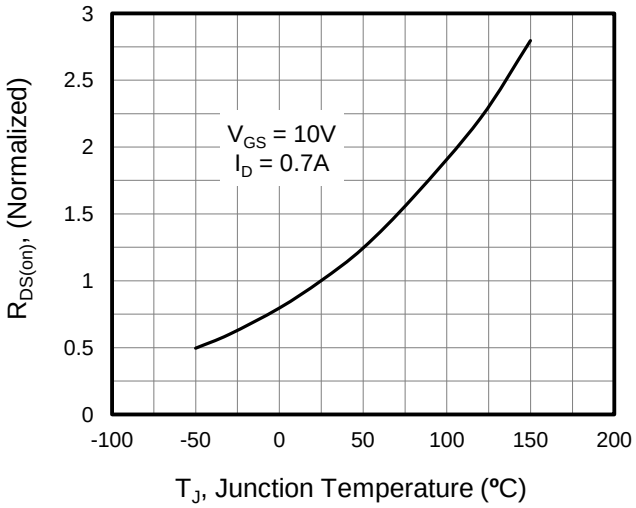


Figure 8. Threshold Voltage vs. Junction Temperature

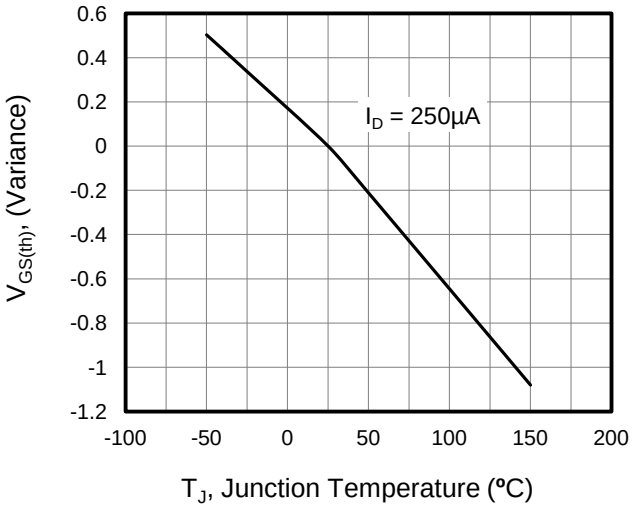


Figure 9. Transient Thermal Impedance TO-220/TO-251/TO-252

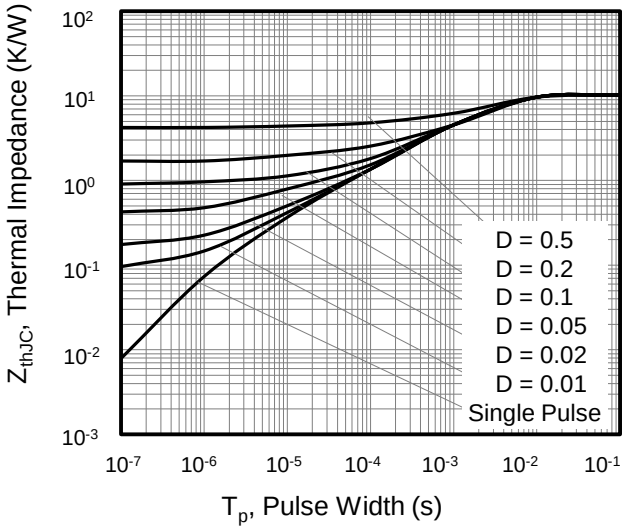


Figure 10. Transient Thermal Impedance TO-220F

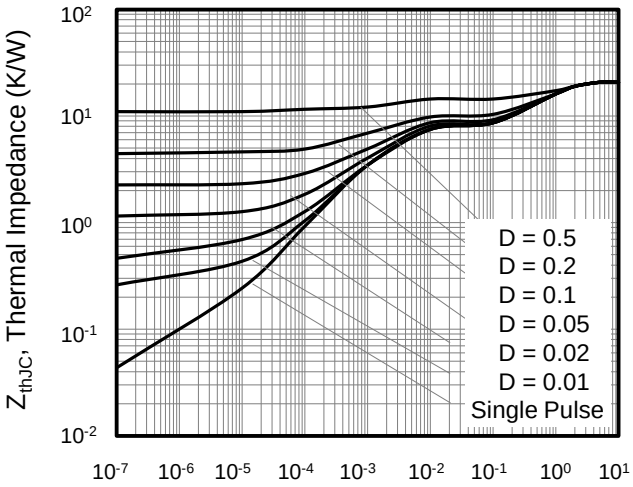


Figure A：Gate Charge Test Circuit and Waveform

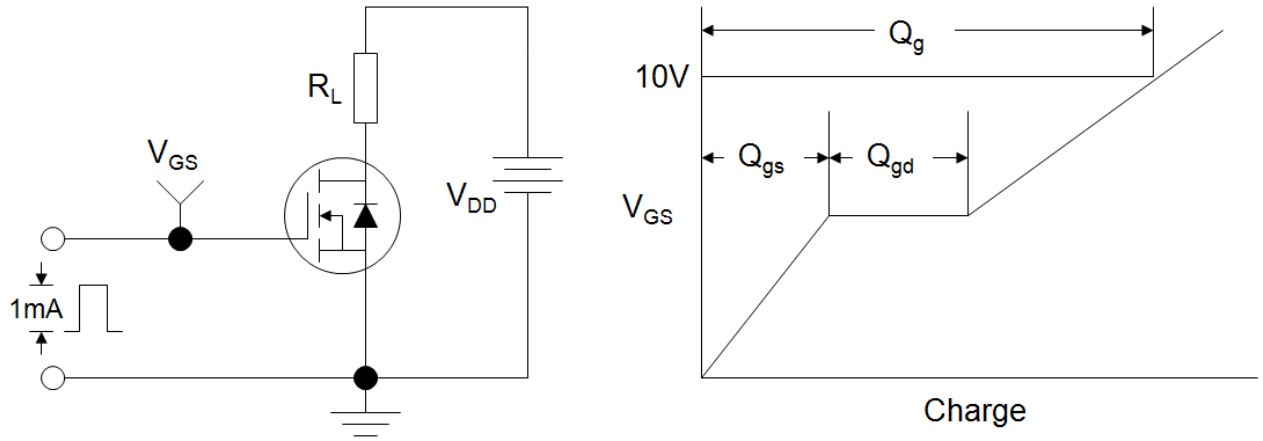


Figure B：Resistive Switching Test Circuit and Waveform

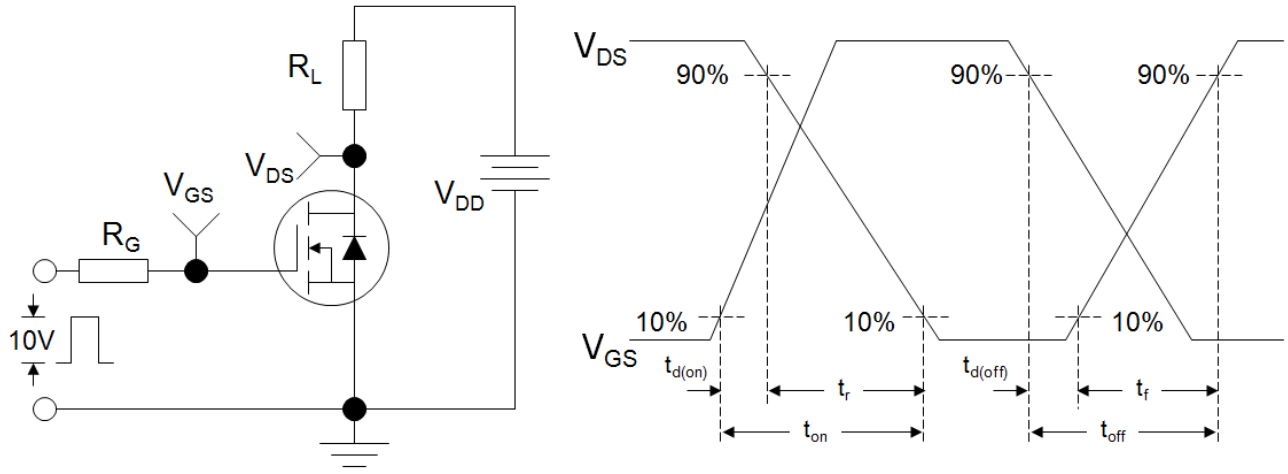
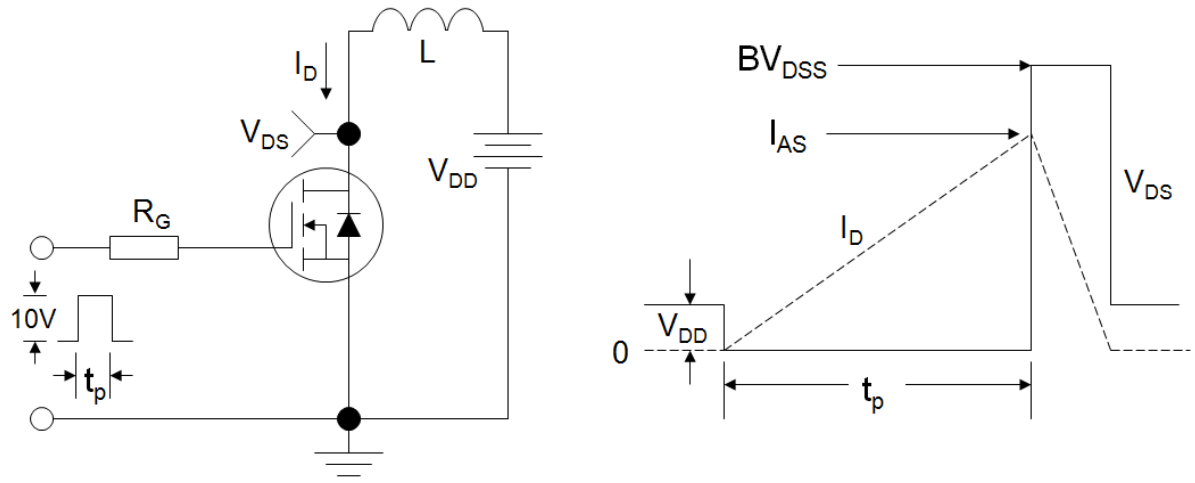
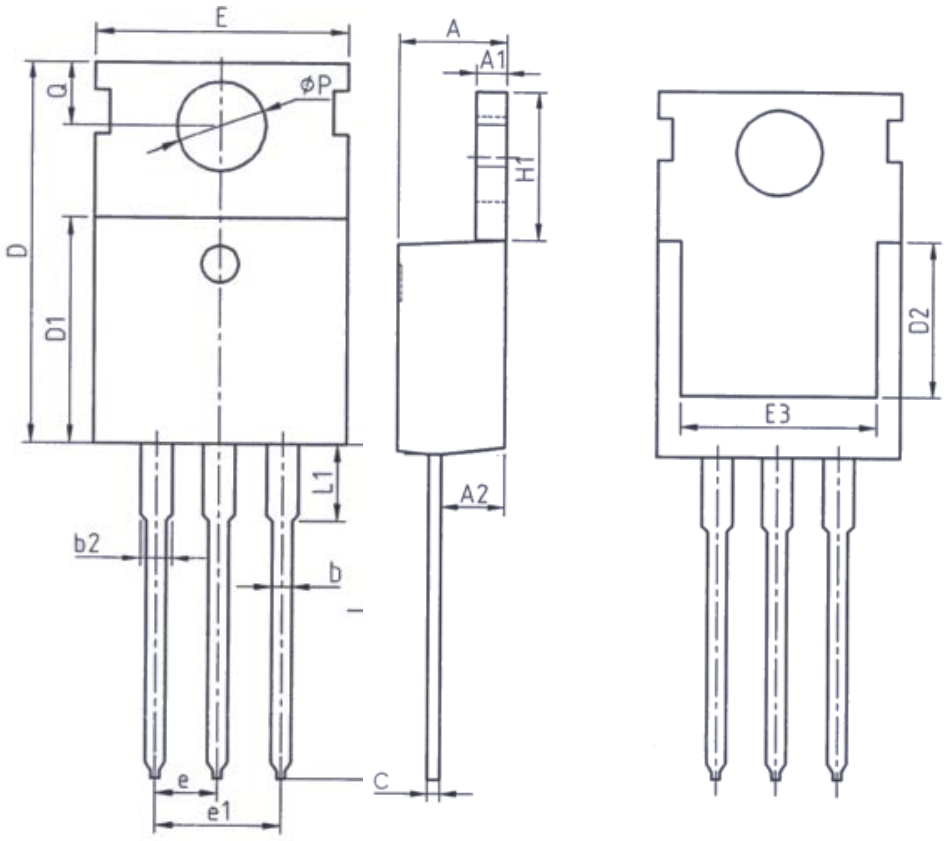


Figure C：Unclamped Inductive Switching Test Circuit and Waveform



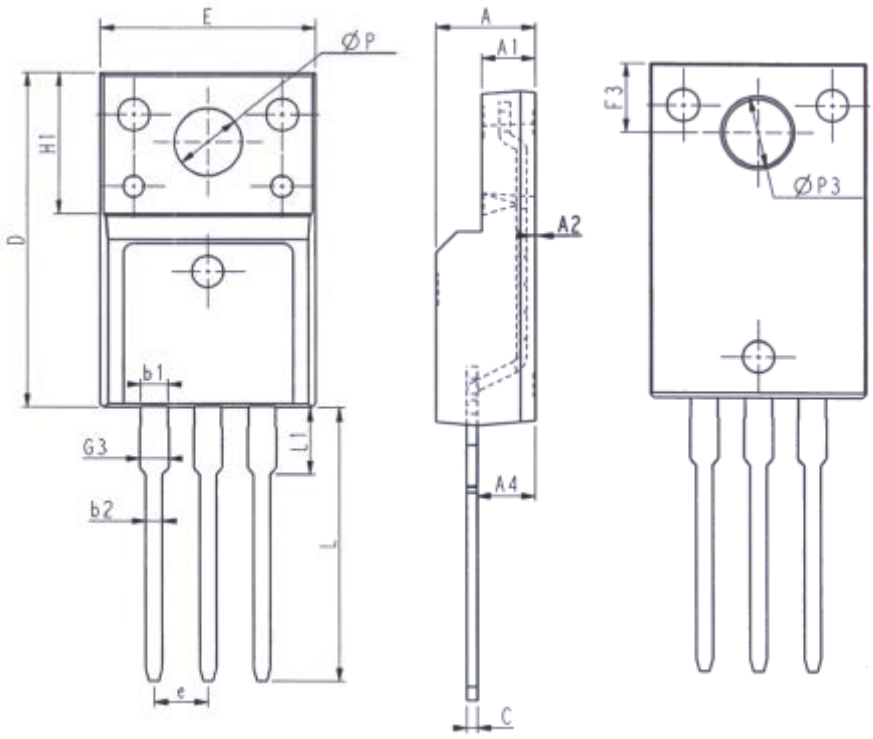
TO-220



Unit: mm		
Symbol	Min.	Max.
A	4.37	4.77
A1	1.25	1.45
A2	2.20	2.60
b	0.70	0.95
b2	1.17	1.47
c	0.40	0.65
D	15.10	16.10
D1	8.80	9.40
D2	5.50	–

Unit: mm		
Symbol	Min.	Max.
E	9.70	10.30
E3	7.00	–
e	2.54BSC	
e1	5.08BSC	
H1	6.25	6.85
L	12.75	13.80
L1	–	3.40
P	3.40	3.80
Q	2.60	3.00

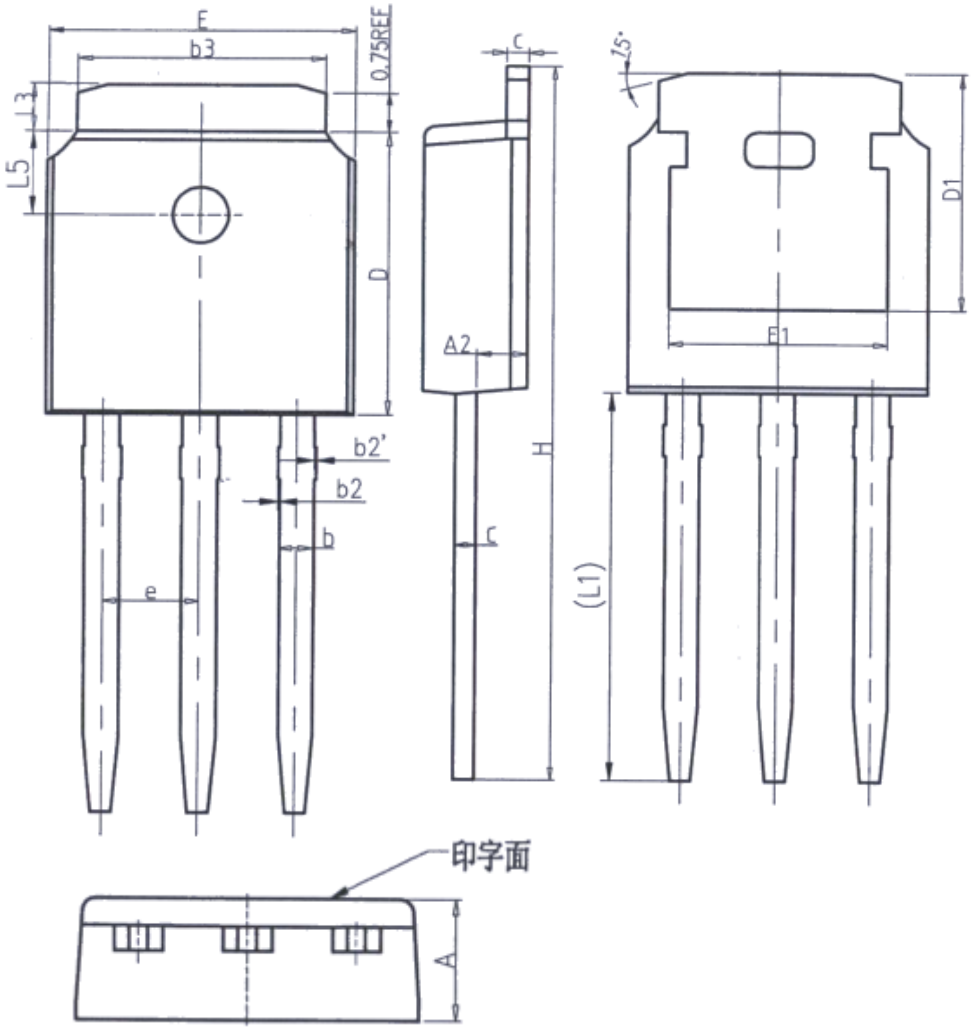
TO-220F



Unit: mm		
Symbol	Min.	Max.
E	9.96	10.36
A	4.50	4.90
A1	2.34	2.74
A2	0.30	0.60
A4	2.56	2.96
c	0.40	0.65
D	15.57	16.17
H1	6.70REF	
e	2.54BSC	

Unit: mm		
Symbol	Min.	Max.
L	12.68	13.28
L1	2.93	3.13
P	3.03	3.38
P3	3.15	3.65
F3	3.15	3.45
G3	1.25	1.55
b1	1.18	1.43
b2	0.70	0.95

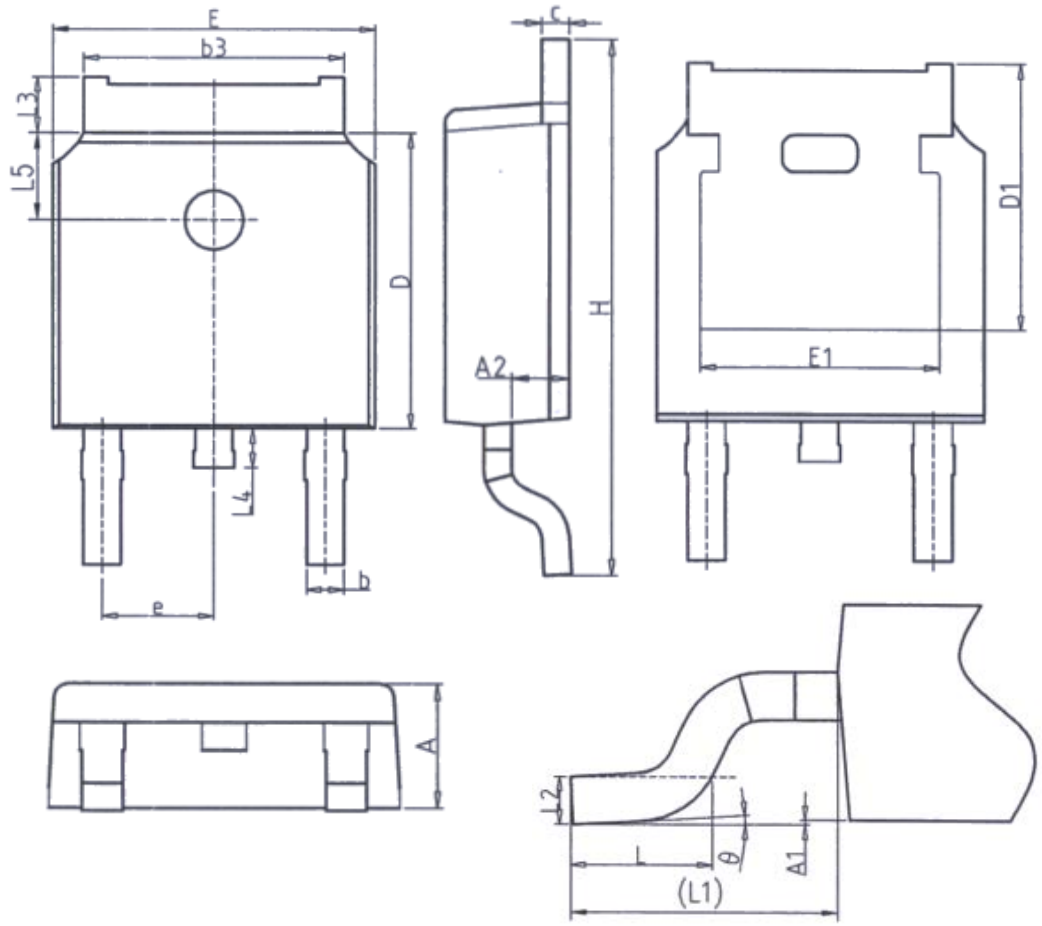
TO-251



Unit: mm		
Symbol	Min.	Max.
A	2.20	2.40
A2	0.97	1.17
b	0.68	0.90
b2	0.00	0.10
b2′	0.00	0.10
b3	5.20	5.50
c	0.43	0.63
D	5.98	6.22

Unit: mm		
Symbol	Min.	Max.
D1	5.30REF	
E	6.40	6.80
E1	4.63	-
e	2.286BSC	
H	16.22	16.82
L1	9.15	9.65
L3	0.88	1.28
L5	1.65	1.95

TO-252



Unit: mm		
Symbol	Min.	Max.
A	2.20	2.40
A1	0.00	0.20
A2	0.97	1.17
b	0.68	0.90
b3	5.20	5.50
c	0.43	0.63
D	5.98	6.22
D1	5.30REF	
E	6.40	6.80
E1	4.63	–

Unit: mm		
Symbol	Min.	Max.
e	2.286BSC	
H	9.40	10.50
L	1.38	1.75
L1	2.90REF	
L2	0.51BSC	
L3	0.88	1.28
L4	–	1.00
L5	1.65	1.95
θ	0°	8°

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